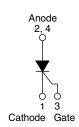


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Vishay Semiconductors

# Thyristor Surface Mount, Phase Control SCR, 16 A





D <sup>2</sup> PAK	(TO-263AB)
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PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub> 16 A								
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V							
$V_{TM}$	1.25 V							
I <sub>GT</sub>	45 mA							
TJ	-40 to +125 °C							
Package	D <sup>2</sup> PAK (TO-263AB)							
Circuit configuration	Single SCR							

#### **FEATURES**

J-STD-020. Meets MSL level 1, LF maximum peak of 245 °C

• Designed qualified and according JEDEC®-JESD 47

COMPLIANT HALOGEN FREE

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-25TTS16S-M3 of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	16.5	25.0						

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	16	۸						
I <sub>RMS</sub>		25	Α						
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V						
I <sub>TSM</sub>		350	Α						
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
T <sub>J</sub>		-40 to +125	°C						

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> , AT 125 °C mA					
VS-25TTS16S-M3	1600	1600	10					



# VS-25TTS16S-M3 Series

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ABSOLUTE MAXIMUM RATINGS									
DADAMETED	SYMBOL	TEC	F CONDITIONS	VAL	LINUTO				
PARAMETER	SYMBOL TEST CONDITIONS		TYP.	UNITS					
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° co	onduction half sine wave	1	6				
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	_			
Maximum peak, one-cycle,		10 ms sine pulse, r	ated V <sub>RRM</sub> applied	30	00	Α			
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, r	10 ms sine pulse, no voltage reapplied						
Maximum 12t for fusing	l <sup>2</sup> t	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	450		A <sup>2</sup> s			
Maximum I <sup>2</sup> t for fusing	I-I	10 ms sine pulse, r	no voltage reapplied	630		A-S			
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms	6300		A²√s				
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.25		V			
On-state slope resistance	r <sub>t</sub>	T 105 °C		12.0		mΩ			
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1.0		V			
Maximum various and direct lookens arrange	1 //	// T <sub>J</sub> = 25 °C		0	.5				
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	10					
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C			00				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear	to 80 %, $V_{DRM} = R_g - k = open$	500		V/µs			
Maximum rate of rise of turned-on current	dl/dt		-			A/µs			

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P <sub>GM</sub>		8.0	W					
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV					
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α					
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	60						
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45	mA					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20						
		Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	2.5						
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	v					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V					
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V reted value	0.25						
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	2.0	mA					

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9						
Typical reverse recovery time	t <sub>rr</sub>	T = 105 °C	4	μs					
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110						

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS								
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case		DC operation	1.1	°C/W					
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	OZ.					
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TT:	S16S					

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

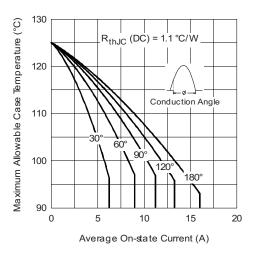


Fig. 1 - Current Rating Characteristics

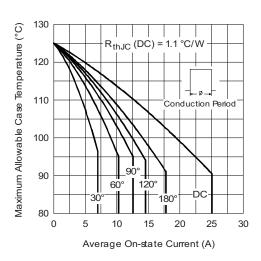


Fig. 2 - Current Rating Characteristics

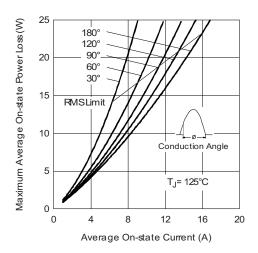


Fig. 3 - On-State Power Loss Characteristics

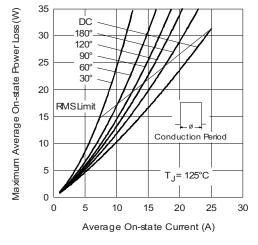


Fig. 4 - On-State Power Loss Characteristics

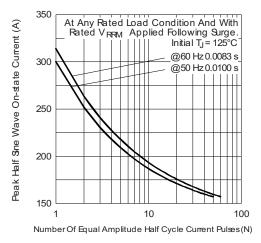


Fig. 5 - Maximum Non-Repetitive Surge Current

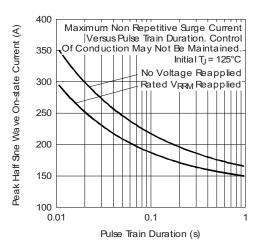


Fig. 6 - Maximum Non-Repetitive Surge Current

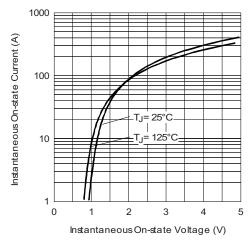


Fig. 7 - On-State Voltage Drop Characteristics

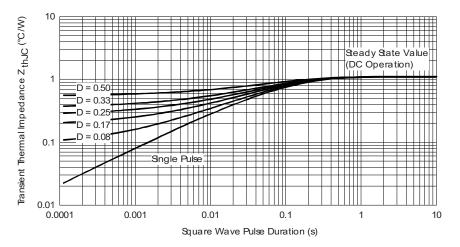


Fig. 8 - Gate Characteristics

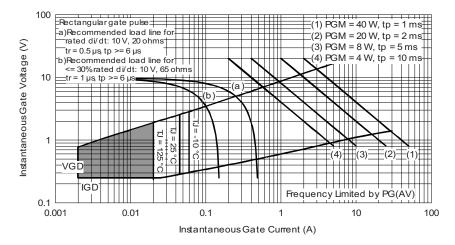
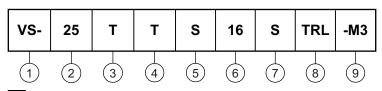


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (25 = 25 A)

- Circuit configuration: T = single thyristor

4 - Package:

 $T = D^2PAK (TO-263AB)$ 

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating: Voltage code x 100 = V<sub>RRM</sub> — 16 = 1600 V

7 - S = surface mountable

8 - • None = tube

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-25TTS16S-M3	50	Antistatic plastic tubes						
VS-25TTS16STRL-M3	800	13" diameter plastic tape and reel						
VS-25TTS16STRR-M3	800	13" diameter plastic tape and reel						

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				



## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES		MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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